

Description

The AU1271D1F-T is a un-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power lines. The AU1271D1F-T complies with the IEC 61000-4-2 (ESD) with ± 30kV air and ± 30kV contact discharge. It is assembled into a SOD-123FL lead-free package. The small size and high ESD/surge protection make AU1271D1F-T an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 12V
- Ultra low clamping voltage
- · Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±30kV
 Contact discharge: ±30kV
 - IEC61000-4-5 (Lightning) 150A (8/20µs)
- RoHS Compliant

Pin Configuration

Mechanical Characteristics

Package: SOD-123FLLead Finish: Matte Tin

Case Material: "Green" Molding Compound.Terminal Connections: See Diagram Below

• Marking Information: See Below

Applications

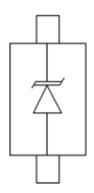
- Fast-charge battery chargers
- Power management system
- · Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals

Marking Information



12A= Device Marking Code

Ordering Information



Circuit and Pin Schematic

Part Number	Packaging	Reel Size	
AU1271D1F-T	3000/Tape & Reel	7 inch	



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

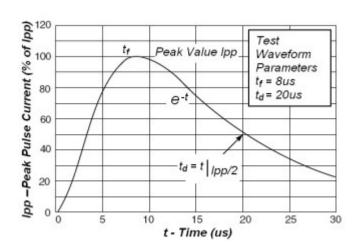
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	4000	W
Peak Pulse Current (8/20μs)	lpp	150	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±30 ±30	kV
Operating Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	Tstg	-40 to +125	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	12.5			V	IT = 1mA
Reverse Leakage Current	I _R			1.0	μΑ	VRWM = 12V
Clamping Voltage	Vc		35		V	IPP = 150A (8 x 20µs pulse)
Junction Capacitance	Сл		600		pF	VR = 0V, f = 1MHz



Typical Performance Characteristics (T_A=25°C unless otherwise Specified)





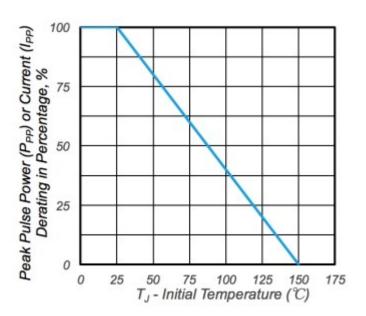
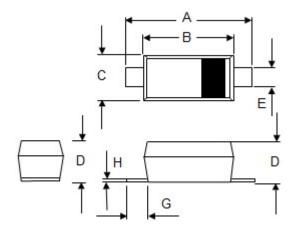


Fig.2 Pulse Derating Cure

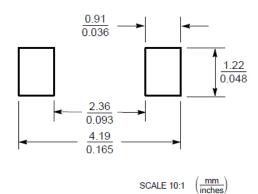


SOD-123FL Package Outline Drawing



	DIMENSIONS					
	MILLIMETERS		INCHES			
SYM	MIN	MAX	MIN	MAX		
Α	3.40	3.95	0.142	0.155		
В	2.50	2.90	0.098	0.114		
С	1.40	1.95	0.055	0.077		
D	0.80	1.00	0.031	0.040		
Е	0.50	1.10	0.020	0.043		
G	0.25	— -	0.010			
Н		0.20		0.008		

Suggested Land Pattern



Contact Information

Applied Power Microelectronics Inc.

Website: http://www.appliedpowermicro.com

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606

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